

1. General description

Ultrafast power diode in a SOT186A plastic package.

2. Features and benefits

- Low forward voltage drop
- Low leakage current
- Soft reverse recovery characteristics
- High thermal cycling performance

3. Applications

- Home appliance power supply
- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)

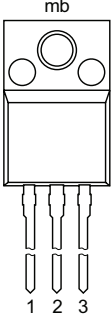
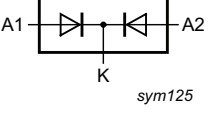
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit
Absolute maximum rating						
V_{RRM}	repetitive peak reverse voltage		600			V
$I_{O(AV)}$	average output current	$\delta = 0.5$; square-wave pulse; $T_h \leq 65$ °C; both diodes conducting; Fig. 1 ; Fig. 2 ; Fig. 3	20			A
I_{FRM}	repetitive peak forward current	$\delta = 0.5$; $t_p = 25$ μ s; $T_h \leq 97$ °C; square-wave pulse ; per diode	20			A
I_{FSM}	non-repetitive peak forward current	$t_p = 10$ ms; $T_{j(init)} = 25$ °C; sine-wave pulse; per diode; Fig. 4	120			A
		$t_p = 8.3$ ms; $T_{j(init)} = 25$ °C; sine-wave pulse; per diode	132			A
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V_F	forward voltage	$I_F = 10$ A; $T_j = 25$ °C; per diode; Fig. 6	-	1.3	1.7	V
		$I_F = 10$ A; $T_j = 150$ °C; per diode; Fig. 6	-	1.0	1.35	V
Dynamic characteristics						
t_{rr}	reverse recovery time	$I_F = 1$ A; $V_R = 30$ V; $di_F/dt = 100$ A/ μ s; $T_j = 25$ °C; per diode; Fig. 7	-	30	50	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A	anode		
2	K	cathode		
3	A	anode		
mb	n.c.	mounting base; isolated		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYV410X-600P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

7. Marking

Table 4. Marking codes

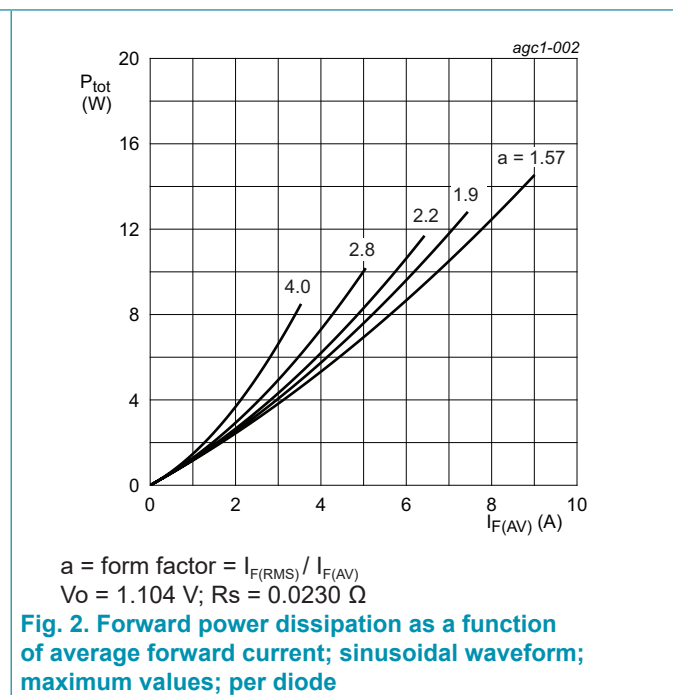
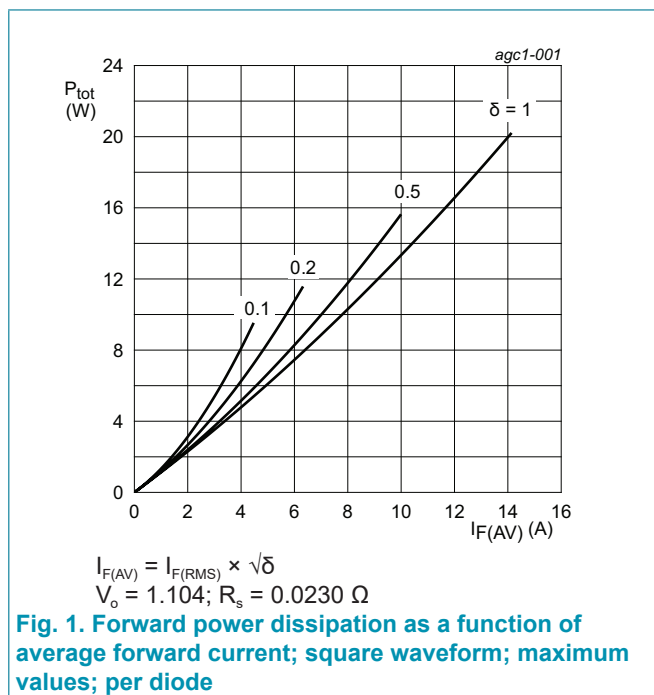
Type number	Marking codes
BYV410X-600P	BYV410X-600P

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	DC	600	V
$I_{O(AV)}$	average output current	$\delta = 0.5$; square-wave pulse; $T_h \leq 65\text{ }^\circ\text{C}$; both diodes conducting; Fig. 1 ; Fig. 2 ; Fig. 3	20	A
I_{FRM}	repetitive peak forward current	$\delta = 0.5$; $t_p = 25\text{ }\mu\text{s}$; $T_h \leq 97\text{ }^\circ\text{C}$; square-wave pulse ; per diode	20	A
I_{FSM}	non-repetitive peak forward current	$t_p = 10\text{ ms}$; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$; sine-wave pulse; per diode; Fig. 4	120	A
		$t_p = 8.3\text{ ms}$; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$; sine-wave pulse; per diode	132	A
T_{stg}	storage temperature		-55 to 175	$^\circ\text{C}$
T_j	junction temperature		175	$^\circ\text{C}$



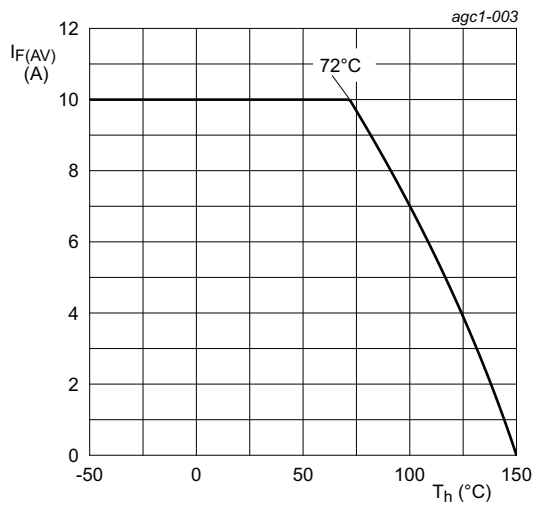


Fig. 3. Forward current as a function of heatsink temperature; maximum values; per diode

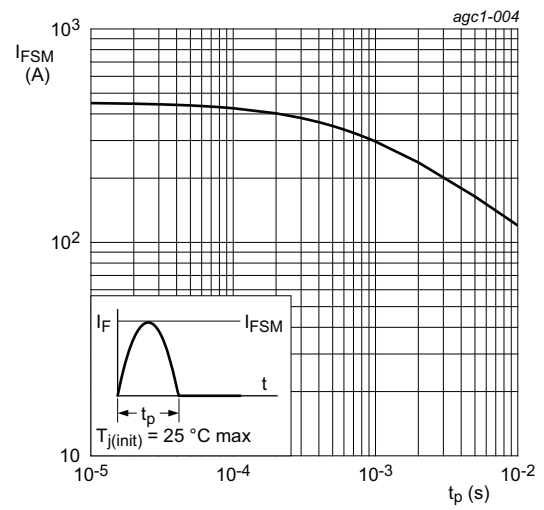


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values; per diode

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	per diode; Fig. 5	-	-	5	K/W
		both diodes conducting; Fig. 5	-	-	3.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

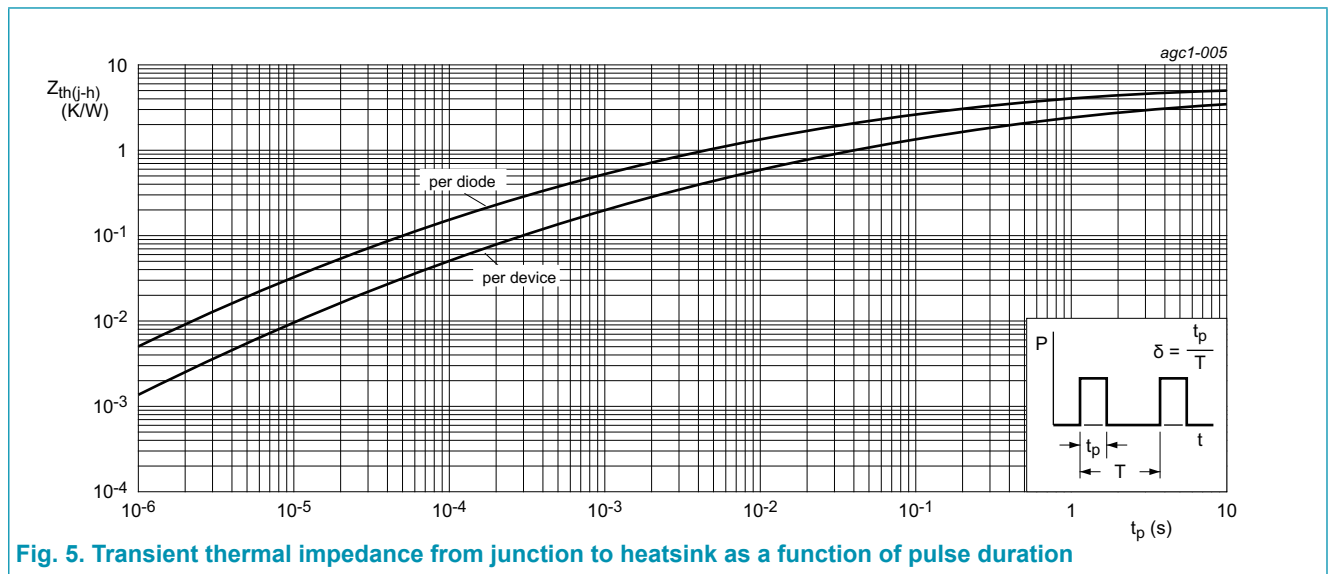


Fig. 5. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Isolation characteristics

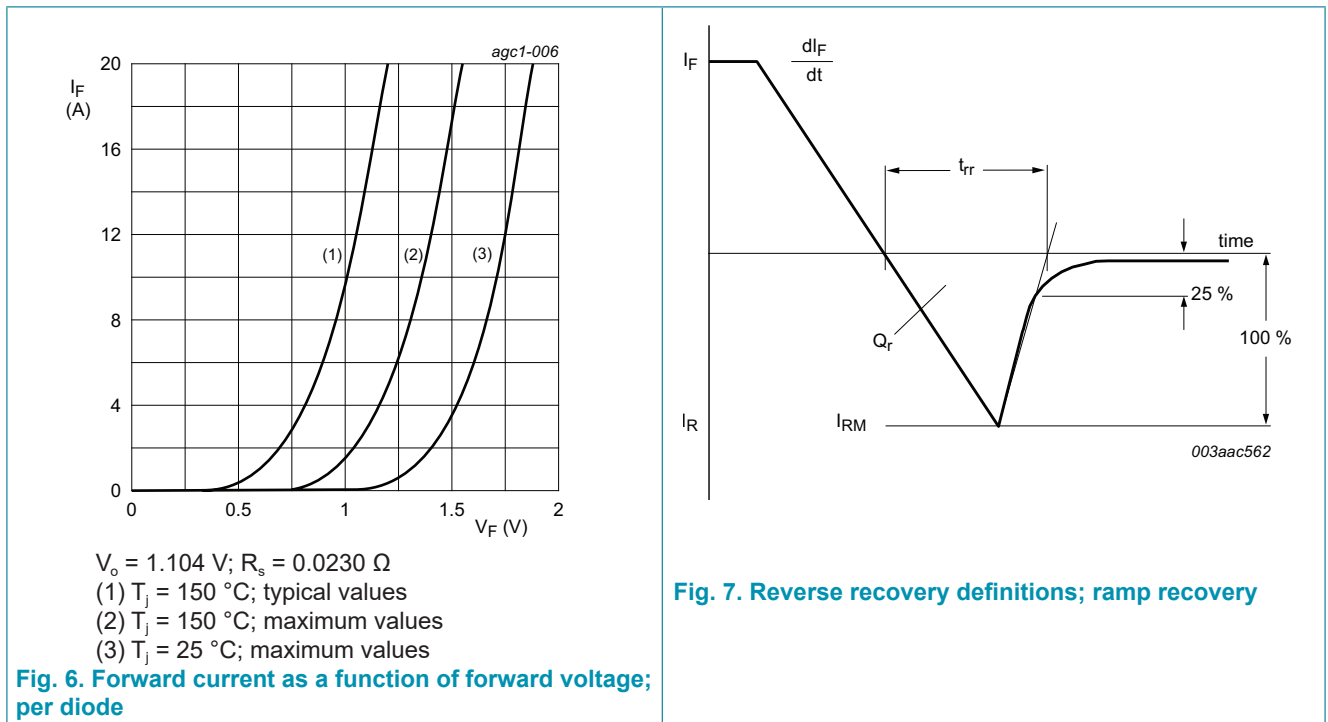
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C_{isol}	isolation capacitance	from cathode to external heatsink	-	10	-	PF

11. Characteristics

Table 8. Characteristics

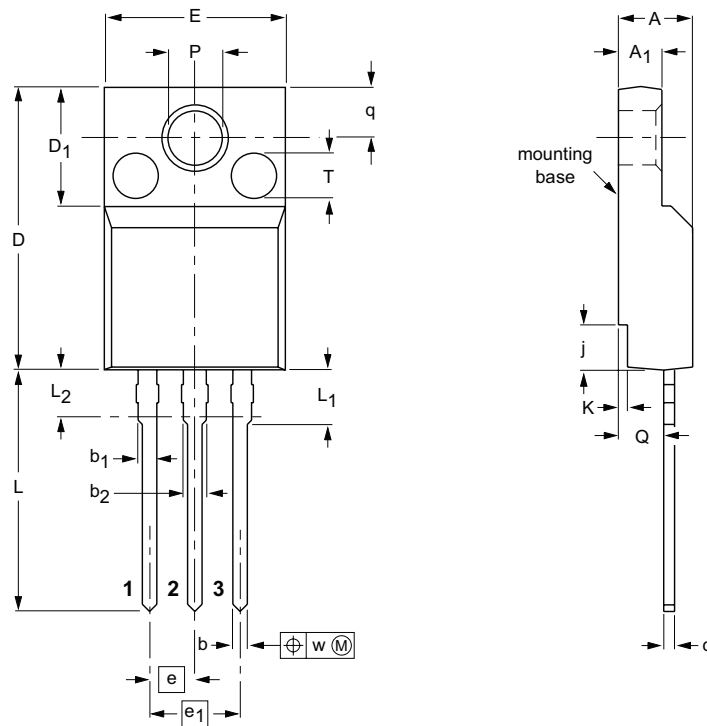
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V_F	forward current	$I_F = 10 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ per diode; Fig. 6	-	1.3	1.7	V
		$I_F = 10 \text{ A}; T_j = 150 \text{ }^\circ\text{C};$ per diode; Fig. 6	-	1.0	1.35	V
		$I_F = 16 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ per diode; Fig. 6	-	1.35	1.75	V
		$I_F = 16 \text{ A}; T_j = 150 \text{ }^\circ\text{C};$ per diode; Fig. 6	-	1.1	1.45	V
I_R	reverse current	$V_R = 600 \text{ V}; T_j = 25 \text{ }^\circ\text{C};$ per diode	-	1	10	μA
		$V_R = 600 \text{ V}; T_j = 150 \text{ }^\circ\text{C};$ per diode	-	0.1	0.5	mA
Dynamic characteristics						
Q_r	reverse charge	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s}; T_j = 25 \text{ }^\circ\text{C};$ per diode; Fig. 7	-	22	-	nC
t_{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s}; T_j = 25 \text{ }^\circ\text{C};$ per diode; Fig. 7	-	30	50	ns
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A}/\mu\text{s}; T_j = 25 \text{ }^\circ\text{C};$ per diode; Fig. 7	-	40	55	ns
		$I_F = 0.5 \text{ A}; I_{rr} = 0.25 \text{ A}; I_R = 1 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ per diode; Fig. 7	-	-	35	ns
I_{RM}	peak reverse recovery current	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s}; T_j = 25 \text{ }^\circ\text{C};$ per diode; Fig. 7	-	1.6	-	A
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A}/\mu\text{s}; T_j = 25 \text{ }^\circ\text{C};$ per diode; Fig. 7	-	1.1	-	A
E_{as}	non-repetitive avalanche energy	$I_R = 4.8 \text{ A}; T_{j(\text{init})} = 25 \text{ }^\circ\text{C}; L = 15 \text{ mH}$	130	175	-	mJ



12. Package outline

Plastic single-ended package; isolated heatsink mounted;
1 mounting hole; 3-lead TO-220 'full pack'

SOT186A



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁	b ₂	c	D	D ₁	E	e	e ₁	j	K	L	L ₁	L ₂ ⁽¹⁾ max.	P	Q	q	T ⁽²⁾	w
mm	4.6 4.0	2.9 2.5	0.9 0.7	1.1 0.9	1.4 1.0	0.7 0.4	15.8 15.2	6.5 6.3	10.3 9.7	2.54	5.08	2.7 1.7	0.6 0.4	14.4 13.5	3.30 2.79	3	3.2 3.0	2.6 2.3	3.0 2.6	2.5	0.4

Notes

- Terminal dimensions within this zone are uncontrolled.
- Both recesses are $\square 2.5 \times 0.8$ max. depth

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT186A		3-lead TO-220F			02-04-09- 06-02-14

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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